NSN 5961-01-054-3757

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-054-3757 **Inclosure Material:** Glass **Overall Length:** Between 0.250 inches and 0.290 inches Overall Diameter: Between 0.090 inches and 0.110 inches **Mounting Method: Terminal Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 12.0 reverse voltage, instantaneous **Current Rating Per Characteristic:** 25.00 milliamperes forward current, total rms peak and 45.00 milliamperes forward current, total rms peak **Power Rating Per Characteristic:** 150.0 milliwatts small-signal input power, common-collector preset **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Test Data Document:** 86197-71216205 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 2 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** Yes - demil/mli

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